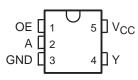
SN74LVC1G126 SINGLE BUS BUFFER GATE WITH 3-STATE OUTPUTS

SCES224C - APRIL 1999 - REVISED FEBRUARY 2000

- EPIC[™] (Enhanced-Performance Implanted CMOS) Submicron Process
- I_{off} Feature Supports Partial-Power-Down Mode Operation
- Supports 5-V V_{CC} Operation
- Package Options Include Plastic Small-Outline Transistor (DBV, DCK) Packages

DBV OR DCK PACKAGE (TOP VIEW)



description

This single bus buffer gate is designed for 1.65-V to 5.5-V V_{CC} operation.

The SN74LVC1G126 is a single bus driver/line driver with a 3-state output. The output is disabled when the output-enable (OE) input is low.

To ensure the high-impedance state during power up or power down, OE should be tied to GND through a pulldown resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

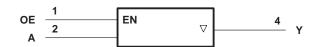
This device is fully specified for partial-power-down applications using I_{off} . The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

The SN74LVC1G126 is characterized for operation from -40°C to 85°C.

FUNCTION TABLE

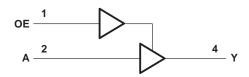
INPUTS		OUTPUT
OE	Α	Y
Н	Н	Н
Н	L	L
L	Χ	Z

logic symbol†



[†]This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	
Input voltage range, V _I (see Note 1)	
Output voltage range, VO (see Notes 1 and 2)	
Input clamp current, I _{IK} (V _I < 0)	
Output clamp current, I _{OK} (V _O < 0)	
Continuous output current, IO	±50 mA
Continuous current through V _{CC} or GND	±100 mA
Package thermal impedance, θ_{JA} (see Note 3): DBV package	347°C/W
DCK package	389°C/W
Storage temperature range, T _{stq}	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 - 2. The value of V_{CC} is provided in the recommended operating conditions table.
 - 3. The package thermal impedance is calculated in accordance with JESD 51.

recommended operating conditions (see Note 4)

			MIN	MAX	UNIT			
V	Supply voltage	Operating	1.65	5.5	V			
VCC	Supply voltage	Data retention only	1.5		V			
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}					
\/	High lovel input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		V			
VIH	High-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$	2		V			
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$	0.7 × V _{CC}					
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}				
\/	Low level input voltage	$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$		0.7	V			
VIL	Low-level input voltage	$V_{CC} = 3 \text{ V to } 3.6 \text{ V}$		0.8	V			
		$V_{CC} = 4.5 \text{ V to } 5.5 \text{ V}$		$0.3 \times V_{CC}$				
٧ _I	Input voltage		0	5.5	V			
٧o	Output voltage		0	VCC	V			
		V _{CC} = 1.65 V		-4				
	High-level output current	V _{CC} = 2.3 V		-8	mA			
lон		Va. 2.V		-16				
		VCC = 3 V		-24				
		V _{CC} = 4.5 V		-32				
		V _{CC} = 1.65 V		4				
		V _{CC} = 2.3 V		8	1			
lOL	Low-level output current		16	mA				
	V _{CC} = 3 V			24				
		V _{CC} = 4.5 V		32				
		V_{CC} = 1.8 V ± 0.15 V, 2.5 V ± 0.2 V		20				
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V			
		$V_{CC} = 5 V \pm 0.5 V$		5				
TA	Operating free-air temperature		-40	85	°C			

NOTE 4: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



PRODUCT PREVIEW

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PAR	RAMETER TEST CONDITIONS		VCC	MIN	түр†	MAX	UNIT	
		I _{OH} = -100 μA	1.65 V to 5.5 V	V _{CC} -0.1				
		$I_{OH} = -4 \text{ mA}$	1.65 V	1.2				
, ,		$I_{OH} = -8 \text{ mA}$	2.3 V	1.9			.,	
VOH		I _{OH} = -16 mA	3 V	2.4			V	
		I _{OH} = -24 mA		2.3				
		I _{OH} = -32 mA	4.5 V	3.8				
		I _{OL} = 100 μA	1.65 V to 5.5 V			0.1		
		I _{OL} = 4 mA	1.65 V			0.45	٧	
,		I _{OL} = 8 mA	2.3 V			0.3		
VOL		I _{OL} = 16 mA	2.1/			0.4		
		I _{OL} = 24 mA	3 V			0.55		
		I _{OL} = 32 mA	4.5 V			0.55		
II	A or OE inputs	V _I = 5.5 V or GND	0 to 5.5 V			±5	μΑ	
l _{off}		V_I or $V_O = 5.5 V$	0			±10	μΑ	
loz		$V_0 = 0 \text{ to } 5.5 \text{ V}$	3.6 V			10	μΑ	
Icc		$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V			10	μΑ	
∆ICC	·	One input at V _{CC} – 0.6 V, Other inputs at V _{CC} or GND	3 V to 5.5 V			500	μΑ	
Ci		$V_I = V_{CC}$ or GND	3.3 V				pF	

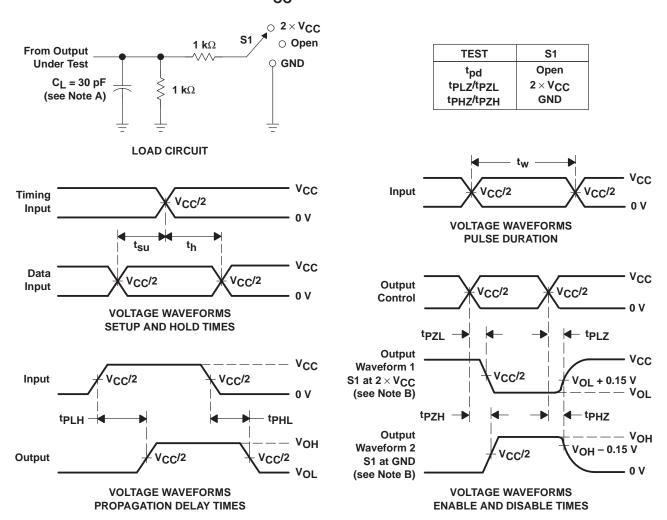
switching characteristics over recommended operating free-air temperature range (unless otherwise noted) (see Figures 1 through 4)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} =		V _{CC} =		VCC =		UNIT
	(INFOT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
^t pd	А	Υ									ns
t _{en}	OE	Υ									ns
^t dis	OE	Y									ns

operating characteristics, T_A = 25°C

PARAMETER TEST CONDITIONS		V _{CC} = 1.8 V	V _{CC} = 2.5 V	V _{CC} = 3.3 V	V _{CC} = 5 V	UNIT	
		TEST CONDITIONS	TYP	TYP	TYP	TYP	UNII
C _{pd}	Power dissipation capacitance	f = 10 MHz					pF

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}$



NOTES: A. C_L includes probe and jig capacitance.

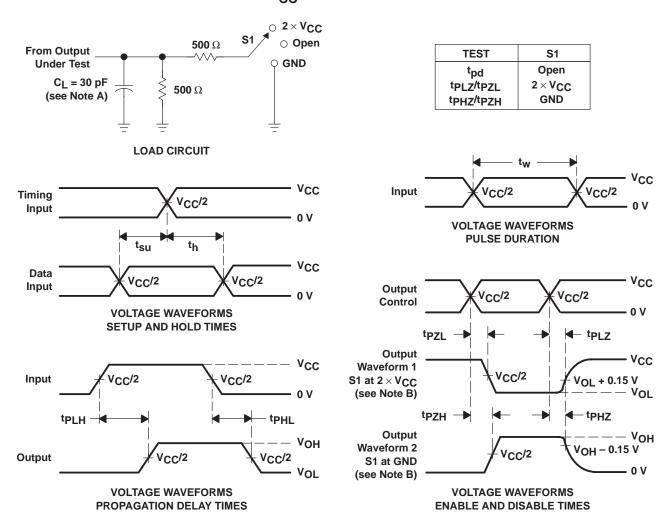
- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2 ns, $t_f \leq$ 2 ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tpl H and tpHI are the same as tpd.

Figure 1. Load Circuit and Voltage Waveforms



PRODUCT PREVIEW

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$

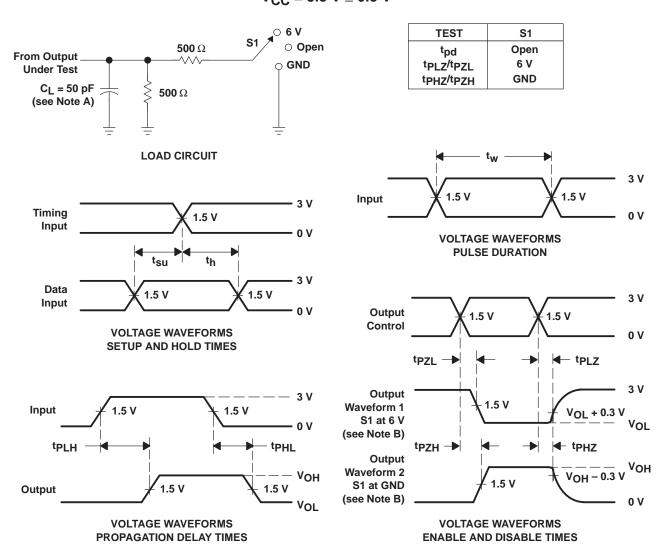


NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq 2$ ns.
- D. The outputs are measured one at a time with one transition per measurement.
- E. tpLz and tpHz are the same as tdis.
- F. tpzL and tpzH are the same as ten.
- G. tplH and tpHL are the same as tpd.

Figure 2. Load Circuit and Voltage Waveforms

PARAMETER MEASUREMENT INFORMATION $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$

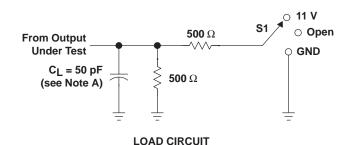


- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_Q = 50 \Omega$, $t_f \leq 2.5 \text{ ns.}$
 - D. The outputs are measured one at a time with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. tpzL and tpzH are the same as ten.
 - G. tpLH and tpHL are the same as tpd.

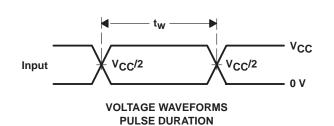
Figure 3. Load Circuit and Voltage Waveforms

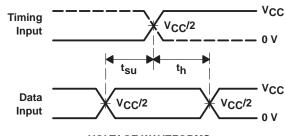


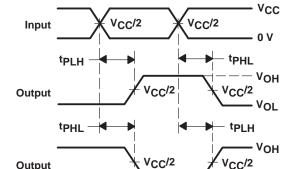
PARAMETER MEASUREMENT INFORMATION $V_{CC} = 5 V \pm 0.5 V$



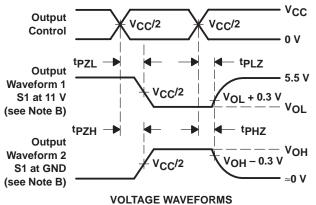
TEST	S1
tPLH/tPHL	Open
tPLZ/tPZL	11 V
tPHZ/tPZH	GND







VOLTAGE WAVEFORMS SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS PROPAGATION DELAY TIMES **INVERTING AND NONINVERTING OUTPUTS**

ENABLE AND DISABLE TIMES LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_I includes probe and jig capacitance.

Output

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, $Z_O = 50 \Omega$, $t_f \leq$ 2.5 ns, $t_f \leq$ 2.5 ns.
- D. The outputs are measured one at a time with one transition per measurement.

V_{CC}/2

VOL

- E. tpLz and tpHz are the same as tdis.
- F. tpZL and tpZH are the same as ten.
- G. tpLH and tpHL are the same as tpd.

Figure 4. Load Circuit and Voltage Waveforms

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